

# Silicon Bridge Rectifier

 $V_{RRM} = 50\text{ V} - 1000\text{ V}$ 
 $I_F = 25\text{ A}$ 

## Features

- High efficiency
- Types up to 1000 V  $V_{RRM}$
- Silicon junction
- Metal case

**KBPC-T/W Package**


## Mechanical Data

Case: Mounted in the bridge encapsulation

Mounting position: Hole for #10 screw

Polarity: Marked on case

**Maximum ratings, at  $T_j = 25\text{ °C}$ , unless otherwise specified (KBPCXXXXT uses KBPC-T package while KBPCXXXXW uses KBPC-W package)**

Parameter	Symbol	Conditions	KBPC2506T/W	KBPC2508T/W	KBPC2510T/W	Unit
Repetitive peak reverse voltage	$V_{RRM}$		600	800	1000	V
RMS reverse voltage	$V_{RMS}$		420	560	700	V
DC blocking voltage	$V_{DC}$		600	800	1000	V
Continuous forward current	$I_F$	$T_C \leq 55\text{ °C}$	25	25	25	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	350	350	350	A
Operating temperature	$T_j$		-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	$T_{stg}$		-55 to 150	-55 to 150	-55 to 150	°C

## Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	KBPC2506T/W	KBPC2508T/W	KBPC2510T/W	Unit
Diode forward voltage	$V_F$	$I_F = 12.5\text{ A}$ , $T_j = 25\text{ °C}$	1.1	1.1	1.1	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ °C}$ $V_R = 50\text{ V}$ , $T_j = 100\text{ °C}$	5 500	5 500	5 500	$\mu\text{A}$

## Thermal characteristics

Parameter	Symbol	Conditions	KBPC2506T/W	KBPC2508T/W	KBPC2510T/W	Unit
Thermal resistance, junction - case	$R_{thJC}$		1.9	1.9	1.9	°C/W

FIG.1 - TYPICAL FORWARD CURRENT DERATING CURVE

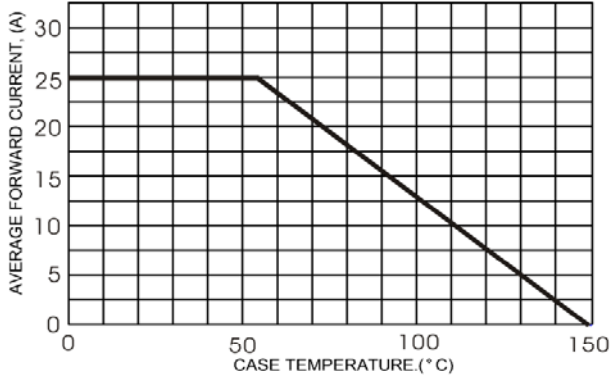


FIG.2 - TYPICAL FORWARD CHARACTERISTICS

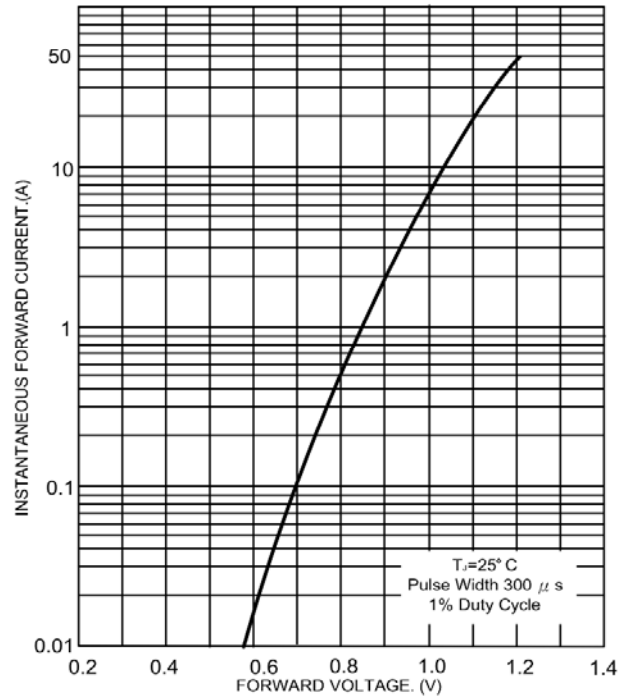


FIG.3 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

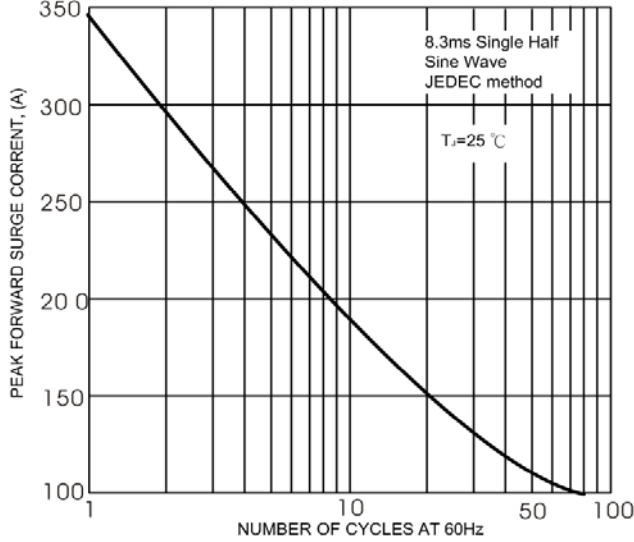


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

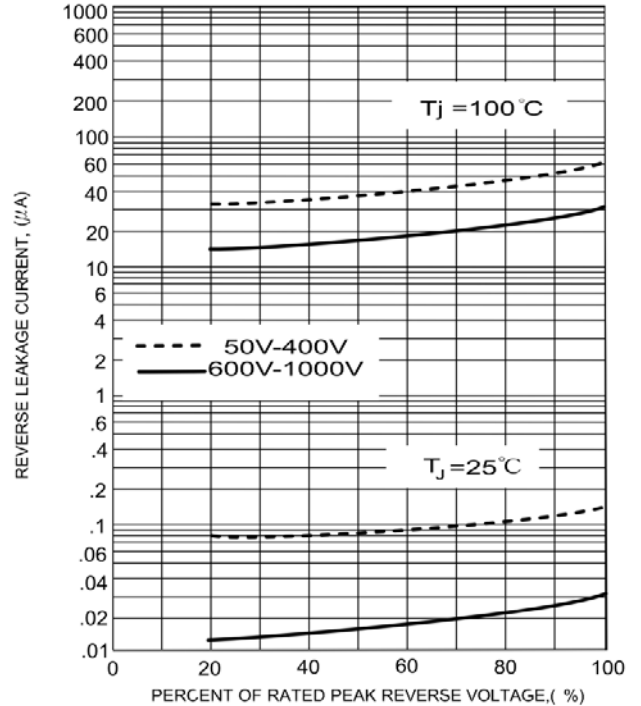


FIG.4 - TYPICAL JUNCTION CAPACITANCE

